

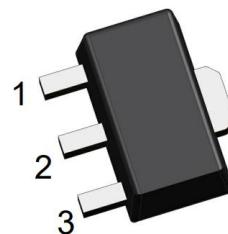
## SSCNX5XGS3

### NPN Plastic-Encapsulate Transistors

#### ➤ Description

This product has the characteristics of high current and high-power consumption. It is universal and suitable for many different applications. It can be used for power amplifiers and switches that require collector currents up to 1A.

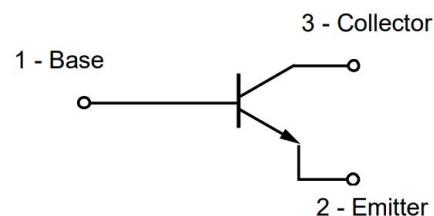
#### ➤ Pin configuration



SOT-89-3L

#### ➤ Features

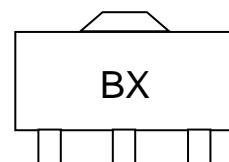
- Driver stages of audio amplifiers
- Linear voltage regulators
- Low-side switches
- Battery-driven devices
- Power management
- MOSFET drivers



Circuit Diagram

#### ➤ Ordering Information

Device	Marking	Package	Shipping
SSCNX54GS3	BA	SOT-89-3L	1000/Reel
SSCNX5410GS3	BC		
SSCNX5416GS3	BD		
SSCNX55GS3	BE		
SSCNX5510GS3	BG		
SSCNX5516GS3	BM		
SSCNX56GS3	BH		
SSCNX5610GS3	BK		
SSCNX5616GS3	BL		



Marking (Top View)

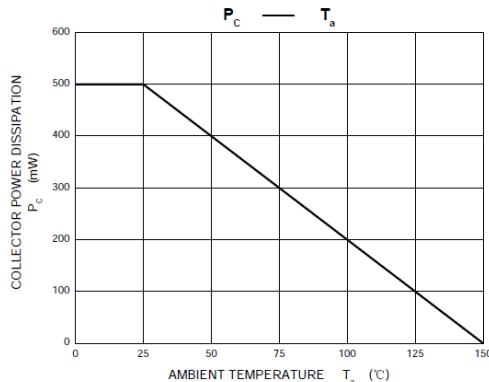
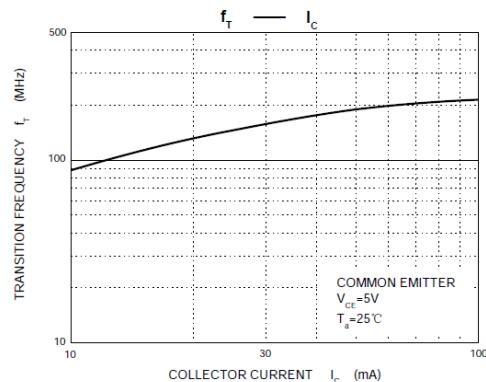
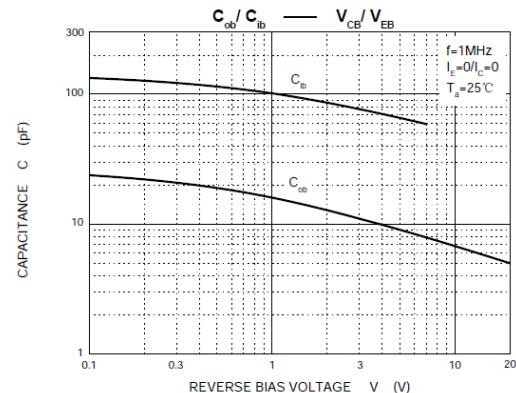
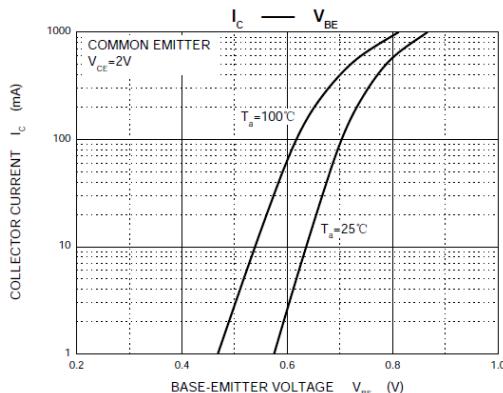
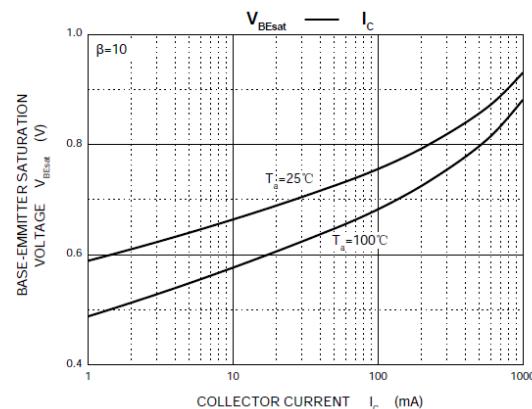
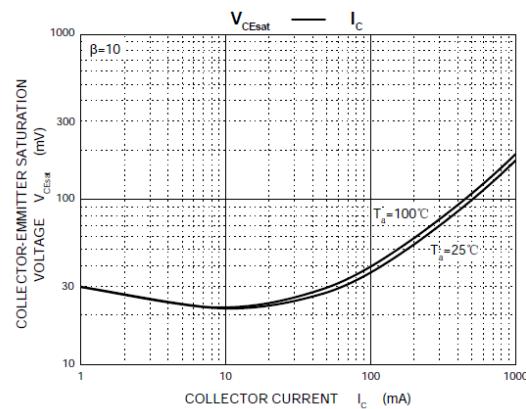
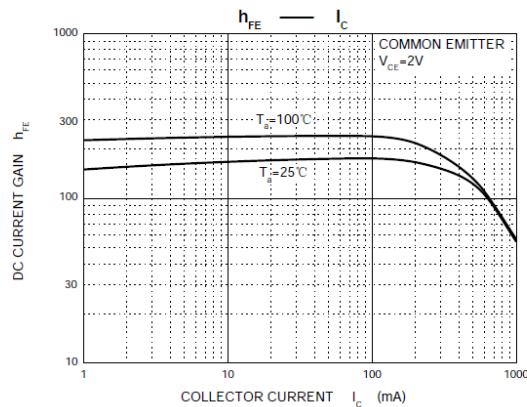
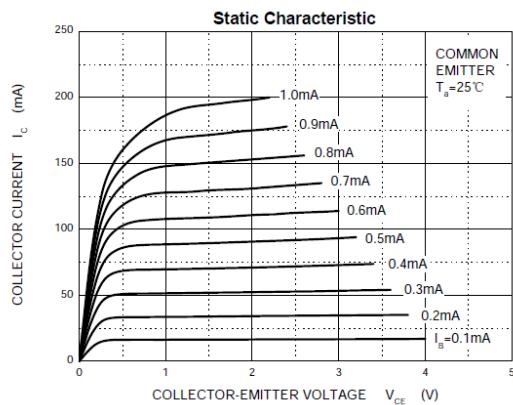
➤ Absolute Maximum Ratings ( $T_A=25^\circ C$  unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage X54 X55 X56	$V_{CBO}$	45	V
		60	
		100	
Collector- Emitter Voltage X54 X55 X56	$V_{CEO}$	45	V
		60	
		80	
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current-Continuous	$I_C$	1	A
Base Current	$I_B$	0.1	A
Collector Power Dissipation	$P_C$	500	mW
Thermal Resistance From Junction To Ambient	$R_{\Theta JA}$	250	°C/W
Junction Temperature	$T_J$	150	°C
Storage Temperature	$T_{STG}$	-55 to 150	°C

➤ Electrical Characteristics ( $T_A=25^\circ C$  unless otherwise noted)

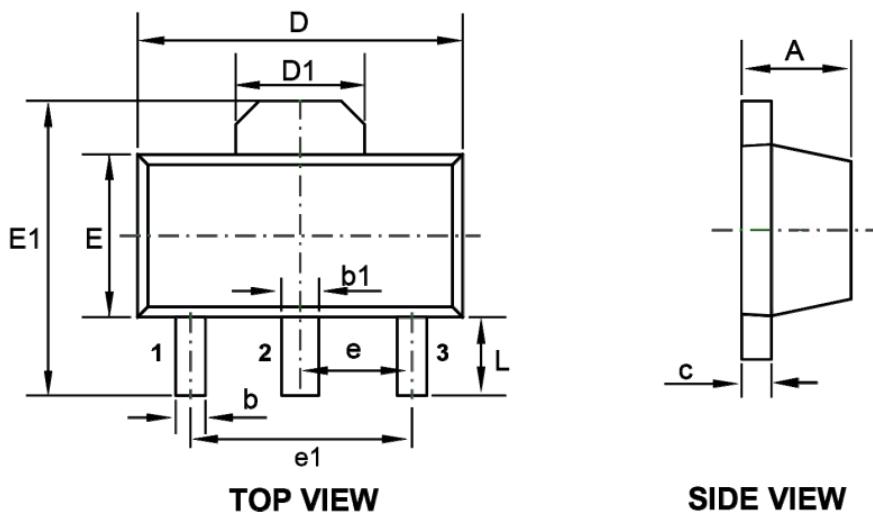
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage X54 X55 X56	$BV_{CBO}$	$I_C=100\mu A, I_E=0$	45			V
			60			
			100			
Collector-emitter Breakdown Voltage X54 X55 X56	$BV_{CEO}$	$I_C=10mA, I_B=0$	45			V
			60			
			80			
Emitter -Base Breakdown Voltage	$BV_{EBO}$	$I_E=10\mu A, I_C=0$	5			V
Collector Cutoff Current	$I_{CBO}$	$V_{CB}=30V, I_E=0$			100	nA
Emitter Cutoff Current	$I_{EBO}$	$V_{EB}=5V, I_C=0$			100	nA
DC Current Gain	$h_{FE1}$	$V_{CE}=2V, I_C=5mA$	40			
DC Current Gain	$h_{FE2}$	$V_{CE}=2V, I_C=150mA$	63		250	
X54, X55, X56			63		160	
X5410, X5510, X5610			100		250	
X5416, X5516, X5616						
DC Current Gain	$h_{FE3}$	$V_{CE}=2V, I_C=0.5A$	25			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=0.5A, I_B=50mA$			0.5	V
Base-Emitter Voltage	$V_{BE}$	$V_{CE}=2V, I_C=0.5A$			1	V
Transition frequency	$f_T$	$V_{CE}=5V, I_C=10mA$ $f=100MHz$		130		MHz

➤ Typical Performance Characteristics ( $T_A=25^\circ\text{C}$  unless otherwise noted)



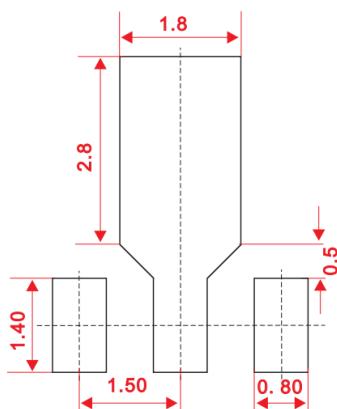
➤ Package Information

● Mechanical Data



DIM	Millimeters		
	Min.	Typ.	Max.
A	1.40	-	1.60
b	0.32	-	0.52
b1	0.40	-	0.58
c	0.35	-	0.44
D	4.40	-	4.60
D1	1.55 REF.		
E	2.30	-	2.60
E1	3.94	-	4.25
e		1.50	
e1		3.00	
L	0.90	-	1.20

● Recommended Pad outline (Unit: mm)



**DISCLAIMER**

AFSEMI RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. AFSEMI DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENCE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

THE GRAPHS PROVIDED IN THIS DOCUMENT ARE STATISTICAL SUMMARIES BASED ON A LIMITED NUMBER OF SAMPLES AND ARE PROVIDED FOR INFORMATIONAL PURPOSE ONLY. THE PERFORMANCE CHARACTERISTICS LISTED IN THEM ARE NOT TESTED OR GUARANTEED. IN SOME GRAPHS, THE DATA PRESENTED MAY BE OUTSIDE THE SPECIFIED OPERATING RANGE (E.G. OUTSIDE SPECIFIED POWER SUPPLY RANGE) AND THEREFORE OUTSIDE THE WARRANTED RANGE.

OUR PRODUCT SPECIFICATIONS ARE ONLY VALID IF OBTAINED THROUGH THE COMPANY'S OFFICIAL WEBSITE, CRM SYSTEM, OR OUR SALES PERSONNEL CHANNELS. IF CHANGES OR SPECIAL VERSIONS ARE INVOLVED, THEY MUST BE STAMPED WITH A QUALITY SEAL AND MARKED WITH A SPECIAL VERSION NUMBER TO BE VALID.